

GSDSBAT42/43XV2

Schottky Barrier Diodes

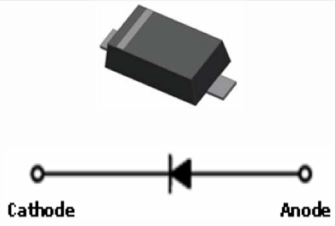
Product Description

Schottky Barrier Diodes 200mW / 30V

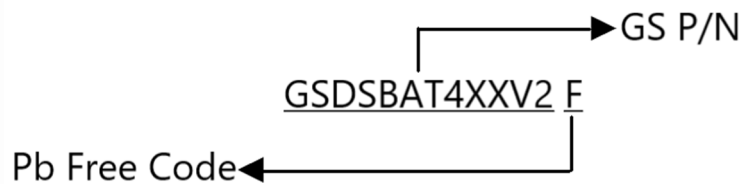
Features

- Low Forward Voltage Drop
- Extremely Small SOD-523 Package
- Flat Lead SOD-523 Small Outline Plastic Package
- Surface Device Type Mounting
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicate Cathode

Marking Information

Part Number	Package	Part Marking	Equivalent Circuit diagram
GSDSBAT42XV2F	SOD-523	6B	
GSDSBAT43XV2F	SOD-523	7B	

Ordering Information



Part Number	Package	Quantity
GSDSBAT42XV2F	SOD-523	3000 PCS
GSDSBAT43XV2F	SOD-523	

Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Symbol	Parameter	Value	Unit
P _D	Power Dissipation	200	mW
V _{RRM}	Repetitive Peak Reverse Voltage	30	V
V _R	Maximum DC Blocking Voltage	30	V
T _J	Operating Junction Temperature	+125	°C
T _{STG}	Storage Temperature Range	-65 to +125	°C
I _{F(AV)}	Average Forward Rectified Current	200	mA
I _{FSM}	Forward current surge peak	4	A

These ratings are limiting values above which the serviceability of the diode may be impaired.

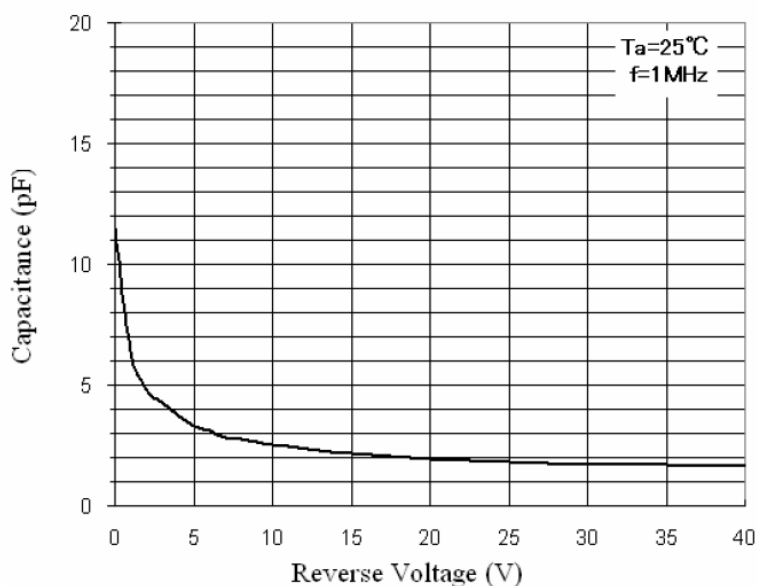
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

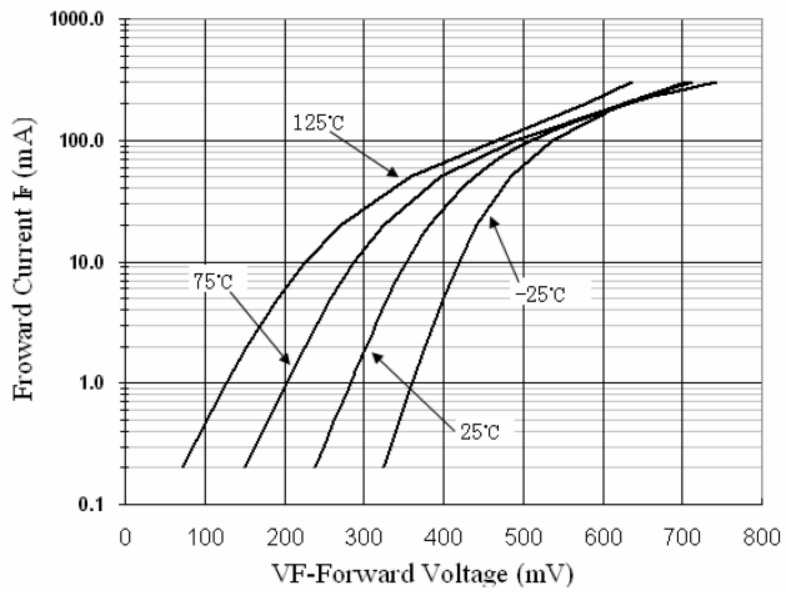
Symbol	Parameter	Test Condition	Min	Max	Unit
B _V	Breakdown Voltage	I _R = 100μA	30	-	V
I _R	Reverse Current	V _R = 25V	-	500	nA
V _F	Forward Voltage	GSDSBAT42XV2 I _F = 10mA	-	0.40	V
		I _F = 50mA	-	0.65	
	GSDSBAT43XV2 I _F = 2mA	0.26	0.33		
	I _F = 15mA	-	0.45		
	GSDSBAT42XV2, GSDSBAT43XV2	I _F = 200mA	-	1.0	
T _{RR}	Reverse Recovery Time	I _F = I _R = 10mA R _L = 100Ω T _{RR} = 1mA	5(Typical)		nS
C	Capacitance	V _R = 1V, f = 1MHZ	7(Typical)		pF

Typical Characteristics

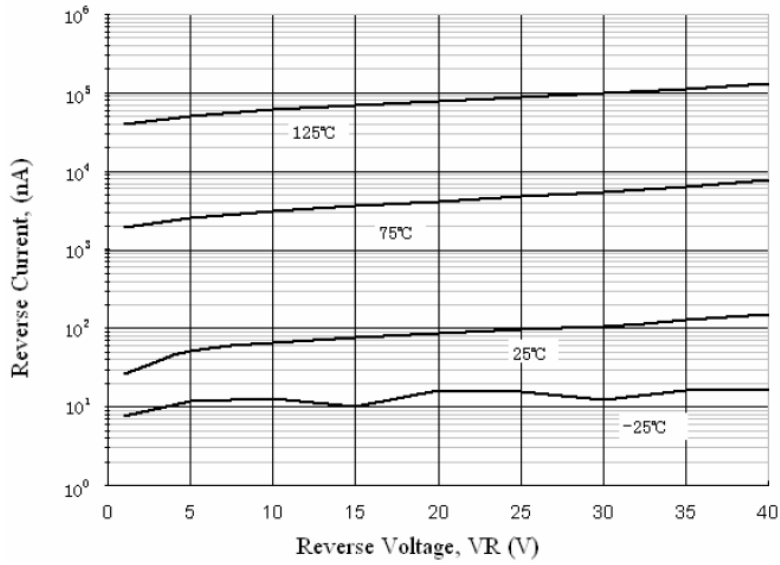
Total Capacitance



Forward Voltage vs Ambient Temperature

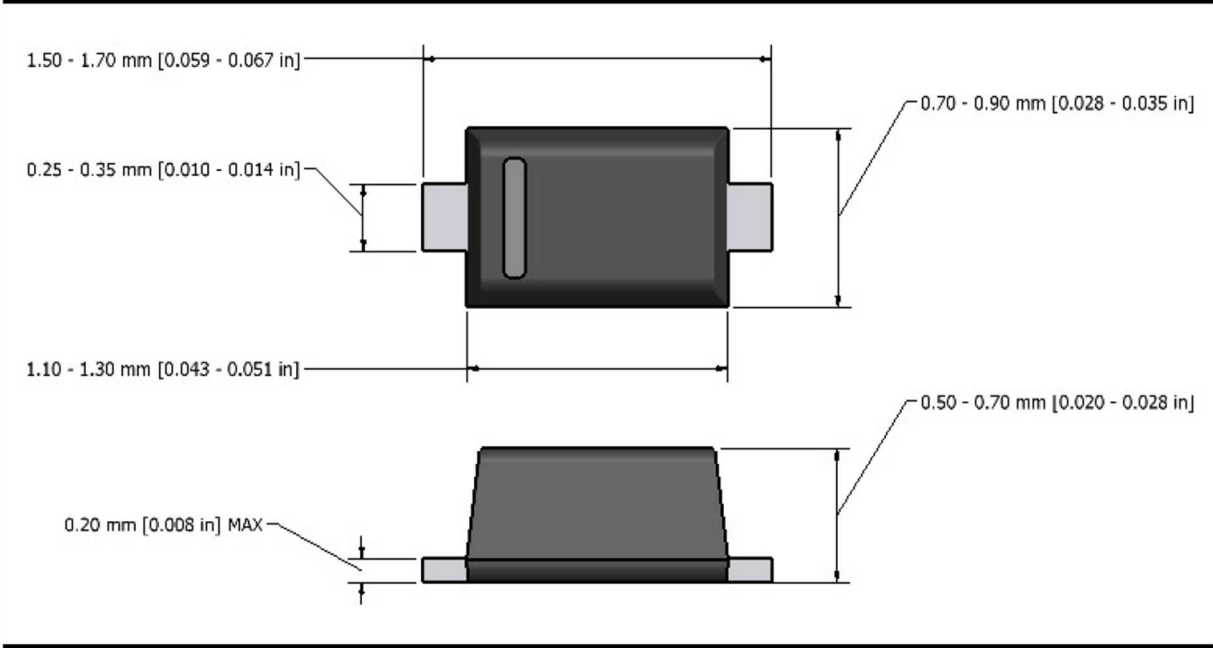


Reverse Current vs Reverse Voltage



Package Dimension

SOD-523







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